

# MPS6515/MMBT6515

## **NPN General Purpose Amplifier**

- This device is designed as a general purpose amplifier and switch.
- The useful dynamic range extends to 100mA as a switch and to 100MHz as an amplifier.





1. Emitter 2. Base 3. Collector 1. Base 2. Emitter 3. Collector

## **Absolute Maximum Ratings\*** T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter		Value	Units
$V_{CEO}$	Collector-Emitter Voltage		25	V
V <sub>CBO</sub>	Collector-Base Voltage		40	V
V <sub>EBO</sub>	Emitter-Base Voltage		4.0	V
I <sub>C</sub>	Collector current - Continue	us	200	mA
T <sub>J</sub> , T <sub>stq</sub>	Junction and Storage Temperature		-55 ~ +150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

  1) These ratings are based on a maximum junction temperature of 150 degrees C.

  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characte	eristics				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 0.5 \text{mA}, I_B = 0$	25		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10\mu A, I_{E} = 0$	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_C = 10\mu A, I_C = 0$	4.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CE} = 30V, I_{E} = 0$		50	nA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0, T = 60°C		1.0	μΑ
On Characte	eristics *	•			
h <sub>FE</sub>	DC Current Gain	$I_C = 2.0 \text{mA}, V_{CE} = 10 \text{V}$ $I_C = 100 \text{mA}, V_{CE} = 10 \text{V}$	250 150	500	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA		0.5	٧
	I Characteristics	·	•	•	•
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 100kHz$		3.5	pF
Pulse Test: Pulse	e Width ≤ 300μs, Duty Cycle ≤ 2.0%	•			

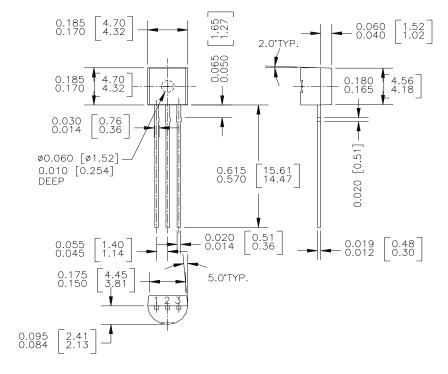
## Thermal Characteristics T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ma	Lluito	
	Parameter	MPS6515	*MMBT6515	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup> Device mounted on FR-4 PCB 1.6" × 0.06"

# **Package Dimensions**

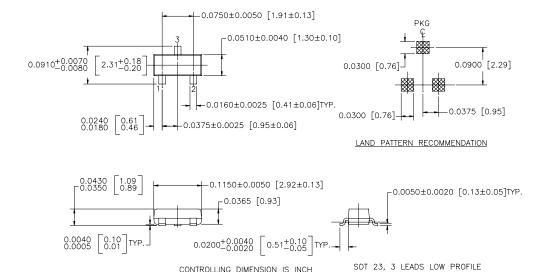
# TO-92



Dimensions in Millimeters

# Package Dimensions (Continued)

# SOT-23



NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

Dimensions in Millimeters

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EnSigna™	I <sup>2</sup> C <sup>TM</sup>	OCX™	RapidConfigure™	UHC™
Across the board.	Around the world.™	OCXPro™	RapidConnect™	UltraFET®
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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#### **Definition of Terms**

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